General Purpose Transistor

NPN Silicon

Features

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CBO}	60	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ι _C	200	mAdc
Collector Current – Peak (Note 3)	I _{CM}	900	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^{\circ}C$ Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

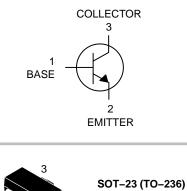
2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

3. Reference SOA curve.



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MARKING DIAGRAM



1AM = Specific Device Code M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

	Device	Package	Shipping [†]
- 1	MMBT3904LT1G	SOT-23	3000 / Tape &
	SMMBT3904LT1G	(Pb-Free)	Reel
- 1	MMBT3904LT3G	SOT-23	10,000 / Tape &
	SMMBT3904LT3G	(Pb-Free)	Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

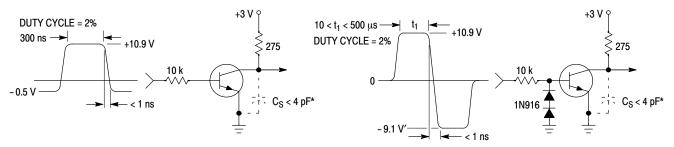
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Chara	acteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•		
Collector – Emitter Breakdown Voltage ($I_c = 1.0 \text{ mAdc}, I_B = 0$)		V _{(BR)CEO}	40	-	Vdc
Collector – Base Breakdown Voltage (I_C	= 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	-	Vdc
Emitter-Base Breakdown Voltage (I _E =	10 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB}	₃ = 3.0 Vdc)	I _{BL}	-	50	nAdc
Collector Cutoff Current ($V_{CE} = 30$ Vdc,	V _{EB} = 3.0 Vdc)	I _{CEX}	-	50	nAdc
ON CHARACTERISTICS (Note 4)			•	-	
		H _{FE}	40 70 100 60 30	- - 300 - -	-
$\begin{array}{l} \mbox{Collector-Emitter Saturation Voltage} \\ (I_C = 10 \mbox{ mAdc}, I_B = 1.0 \mbox{ mAdc}) \\ (I_C = 50 \mbox{ mAdc}, I_B = 5.0 \mbox{ mAdc}) \end{array}$		V _{CE(sat)}		0.2 0.3	Vdc
$\begin{array}{l} \text{Base-Emitter Saturation Voltage} \\ (I_{C} = 10 \text{ mAdc}, I_{B} = 1.0 \text{ mAdc}) \\ (I_{C} = 50 \text{ mAdc}, I_{B} = 5.0 \text{ mAdc}) \end{array}$		V _{BE(sat)}	0.65 -	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain - Bandwidth Product (I _C =	= 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	-	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	-	4.0	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_{C} = 0.5$	C _{ibo}	-	8.0	pF	
Input Impedance (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)		h _{ie}	1.0	10	kΩ
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)		h _{re}	0.5	8.0	X 10 ⁻⁴
Small-Signal Current Gain (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)		h _{fe}	100	400	-
Output Admittance (V_{CE} = 10 Vdc, I_{C} = 1.0 mAdc, f = 1.0 kHz)		h _{oe}	1.0	40	μmhos
Noise Figure (V _{CE} = 5.0 Vdc, I _C = 100 μ Adc, R _S = 1.0 k ohms, f = 1.0 kHz)		NF	-	5.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	$(V_{00} = 3.0)/dc$ $V_{05} = -0.5 //dc$	t _d	_	35	

Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc},$	t _d	-	35	20
Rise Time	$I_{\rm C} = 10 \text{ mAdc}, I_{\rm B1} = 1.0 \text{ mAdc})$	t _r	-	35	ns
Storage Time	(V _{CC} = 3.0 Vdc,	t _s	-	200	20
Fall Time	$I_{C} = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	t _f	Ι	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

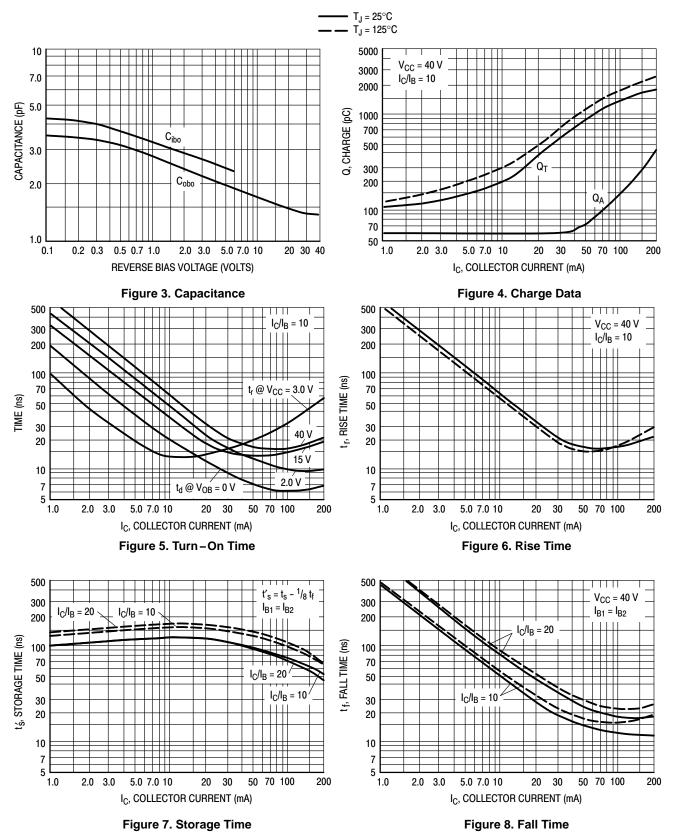
4. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



* Total shunt capacitance of test jig and connectors

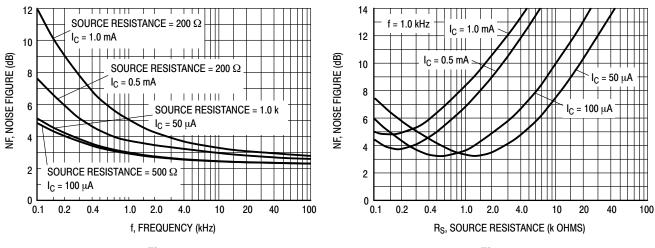
Figure 1. Delay and Rise Time Equivalent Test Circuit Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



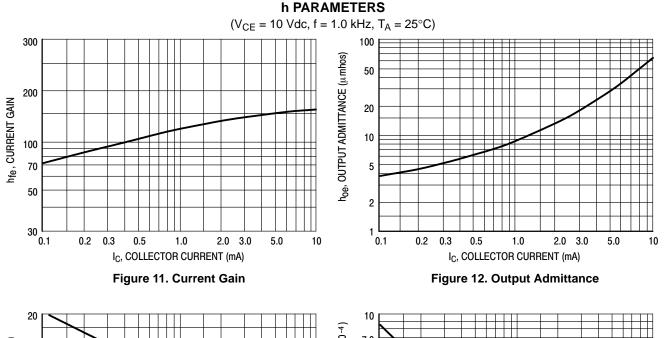
TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

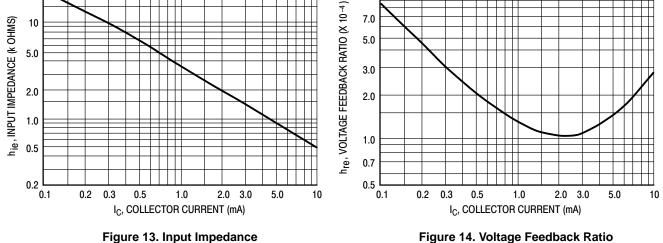
(V_{CE} = 5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)











TYPICAL STATIC CHARACTERISTICS

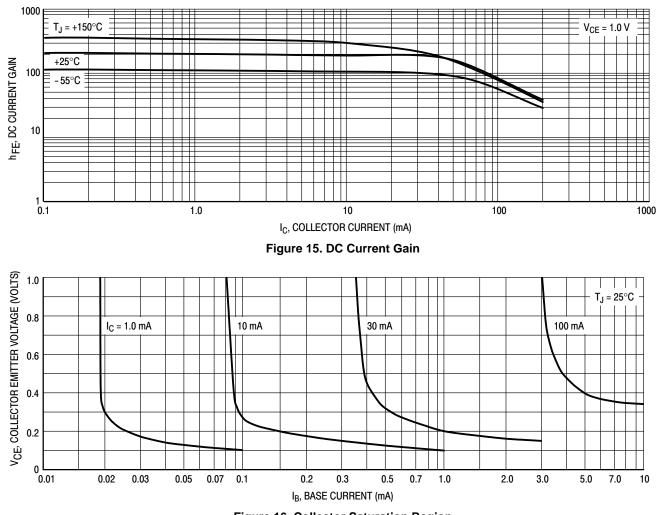
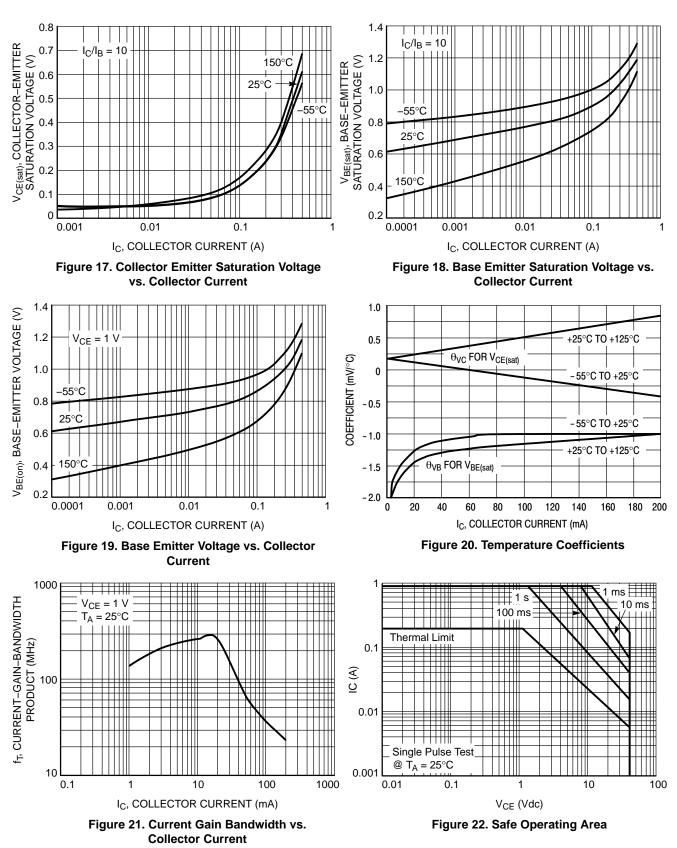


Figure 16. Collector Saturation Region







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